

P. López-Ruiz^a, N. Ordás^a, S. Lindig^b, F. Koch^b, C. García-Rosales^a

^aCEIT and Tecnun (University of Navarra), E-20018 San Sebastian, Spain

^bMax-Planck-Institut für Plasmaphysik, EURATOM Association, D-85748 Garching, Germany

Introduction

Tungsten and tungsten alloys → candidate materials for the **first wall (FW)** armour of future fusion reactors (**DEMO**).

Important safety concern: loss-of-coolant accident with simultaneous air ingress into reactor vessel → ↑ temperature up to 1000 °C in the in-vessel components due to decay heat → **evaporation of radioactive (WO₃)_x-clusters**.

➔ **Addition of stable oxide-forming alloying elements to W** → **self-passivating oxide layer** prevents further W oxidation.

Thin films W-alloys:

- Different binary and ternary W-alloys produced by **magnetron sputtering** exhibit self-passivating behaviour. **WCr10Si10** (wt.%) → **oxidation rate (k_p) three orders of magnitude lower than pure W** up to 1000 °C.
- Si-free alloys (**WCr12Ti2.5**) even lower k_p than WCr10Si10, while brittle silicides avoided ⇒ **See poster: P23B**
- But magnetron sputtering not applicable to DEMO: thickness of several mm required → **Powder metallurgical route**

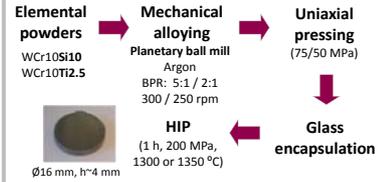
Previous work on bulk W-alloys:

- First **WCr10Si10** samples produced by mechanical alloying (MA) in SPEX mill + hot isostatic pressing (HIP). Main phase **(W,Cr)₅Si₃** + large W grains
- First **oxidation tests**: ↓ parabolic oxidation rate at 600 °C but ↑ at 1000 °C compared to thin films. ≠ oxide scale in thin films (**Cr₂WO₆**) and bulk W-alloys (**Cr₂O₃**) → ≠ oxidation mechanism ➔ Large pure W grains must be avoided.

Aim of this work: Manufacturing of self-passivating bulk **W-Cr-Si** (optimization) and **W-Cr-Ti** (first trials) alloys by **PM: MA (Planetary ball mill)+ HIP**.

Experimental

Manufacturing:



Materials characterization:

- FEG-SEM, EDX mapping, FIB and XRD.
- Open porosity by He pycnometry.
- Vickers microhardness (9.8 N for 15 s).
- Impurities content (O and C by LECO).
- Thermal conductivity Netzsch LFA 427.

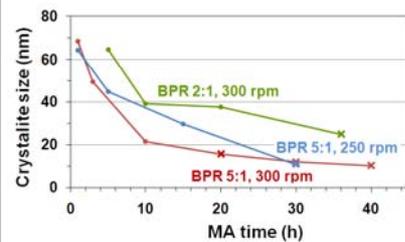
Mechanical alloying

XRD of WCr10Si10 (BPR 5:1, 300 rpm)

- **10 h:** incipient alloying; **shoulder of new phase** on high angle side of 40,2° W peak.
- **20-40 h:** **progress in alloying (not completed)**, broad peaks at 40-50° and 65-70° → silicides + pure W.

*BPR: Ball-to-powder weight ratio

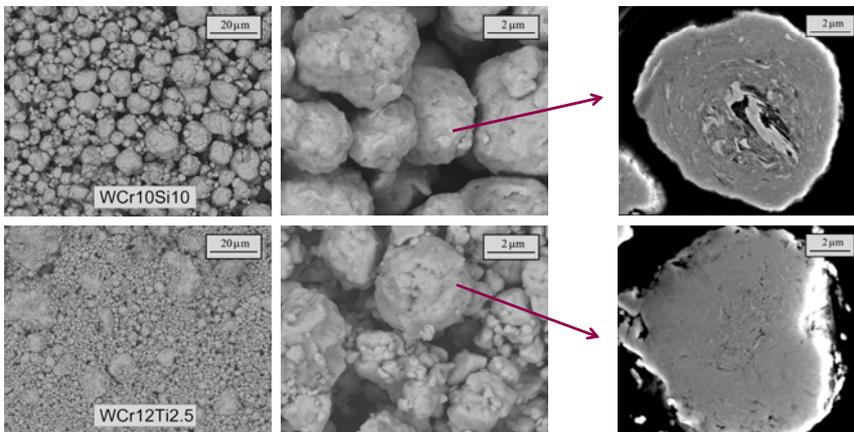
Crystallite size vs. milling time



XRD of WCr12Ti2.5 (BPR 5:1, 250 rpm)

- **5 h:** alloying not started (Cr peaks still visible).
- **15 h:** alloying starts → new metastable bcc phase appears, pure W present.
- **30 h:** **alloying almost complete** → majority ternary bcc phase (solid solution of W, Cr and Ti) + residual pure W.

Powder (BPR 5:1, 250rpm, 30h)

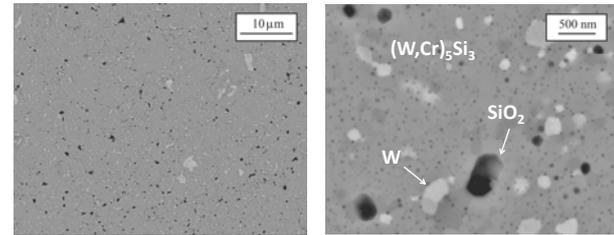


- **WCr10Si10:** Bimodal particle size distribution → ~ steady-state. **Core:** flattened pure W coarsely mixed with Cr and Si; cold welding with progressively finer layered powder → **shell:** very fine microstructure, spec. at surface: true alloying.
- **WCr12Ti2.5:** Broad particle size distribution → no equilibrium of cold welding and fracture, large fraction of very small particles. **Core:** pure W flakes hardly distinguishable, fine microstructure. **Shell:** ternary phase + scarce small W flakes; much finer microstructure.

Composition	Stops	O (wt.%)	C (wt.%)
WCr10Si10	Yes	0.40	0.022
	No	0.123	0.026
WCr12Ti2.5	Yes	0.40	0.034
	No	0.114	0.014

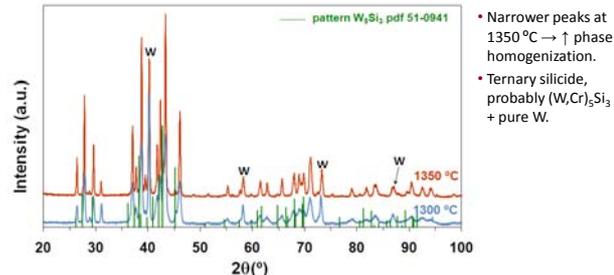
- Starting powders (0.065 % O, 0.006 % C).
- Low impurities content after MA.
- Stops for sampling → ↑ O content, C not influenced.

HIP



WCr10Si10 (BPR 5:1, 300rpm, 20 h) HIPed at 1300 °C

- Fine and homogeneous microstructure; larger W grains from milled particles remain almost unchanged after HIP.
- Ultrafine-ODS intergranular phase inhibit grain growth.
- Similar microstructure at 1300 and 1350 °C (no grain growth).

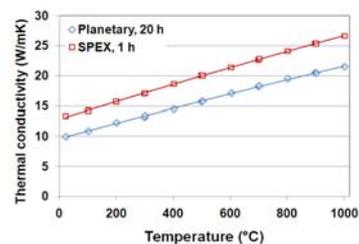


- Narrower peaks at 1350 °C → ↑ phase homogenization.
- Ternary silicide, probably (W,Cr)₅Si₃ + pure W.

- Densification > 95%.
- Hardness typical for silicides (much higher than pure W).

HIP temp. (°C)	Density (%)	HV 1.0
1300	95.2	1414
	100	---
1350	96.6	1374

Thermal conductivity



- Sample from planetary slightly lower conductivity → much finer microstructure ⇒ largely enhanced density of grain boundaries.
- Low thermal conductivity but enough for application at blanket FW.

Conclusions

- Bulk **WCr10Si10** alloys produced by MA (Planetary) + HIP → densities > 95%.
 - MA at **BPR 5:1, 250 rpm, 30 h** → effective milling, low contamination.
 - Core of large powder particles shows heterogeneous phase distribution → after HIP large pure W flake-like grains remaining. Alloying not completed: silicides + W → more work required to further improve microstructure.
 - Nevertheless, **microstructure significantly refined** compared to previous work → **enhanced oxidation resistance expected**.
- First results on MA of **WCr12Ti2.5**:
 - **Very homogeneous structure** inside powder particles.
 - **Ternary metastable bcc phase** + traces of W.
 - A very fine and homogeneous microstructure besides better thermal and mechanical properties than WCr10Si10 can be expected after HIPing.